

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	44	electromagnetic near3 noise near3 suppressor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/18 12:20
S2	1053	electromagnetic near3 noise near3 (shield or shielding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/11 16:33
S3	238521	(vapor near3 deposition) or vapor-deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/06/11 12:00
S4	50	S2 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 13:25
S5	33	S4 and (polymer or resin or rubber)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/11 16:33
S6	16	electromagnetic near3 radiation near3 suppressor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/11 16:32
S7	247725	(vapor near3 deposition) or vapor-deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/11 16:32
S8	2	S7 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/11 16:32
S9	3077	electromagnetic near3 radiation near3 (shield or shielding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 08:38
S10	230	S7 and S9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/11 16:33
S11	192	S10 and (polymer or resin or rubber)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/11 16:33

S12	44	electromagnetic near3 noise near3 suppressor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 13:20
S13	1093	electromagnetic near3 noise near3 (shield or shielding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 08:38
S14	16	electromagnetic near3 radiation near3 suppressor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 08:38
S15	3077	electromagnetic near3 radiation near3 (shield or shielding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 08:38
S16	4125	S12 or S13 or S14 or S15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 08:38
S17	247725	(vapor near3 deposition) or vapor-deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 08:39
S18	284	S16 and S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 08:39
S19	14	S18 and (flame near3 retardant)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 08:54
S20	77	S16 and (flame near3 retardant)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 08:55
S21	2116	(halogen near3 free) same (flame near3 retardant)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 09:11
S23	18	S21 same benefit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 09:11
S24	1167	(halogen near3 non) same (flame near3 retardant)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 09:11
S25	2	S24 same benefit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 10:25

S26	38	"5864088" or "6448491"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/17 15:09
S27	10	S26 and deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 12:54
S30	241	174/350.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 12:53
S31	20	S30 and deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 13:26
S33	3	174/35 near3 ms	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 13:16
S34	130	174/391.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 13:25
S35	21	S34 and deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/12 13:26
S36	25	((TOSHIYUKI) near2 (KAWAGUCHI)).INV.	US-PGPUB; USPAT	OR	ON	2007/10/12 13:46
S37	94	((HIRONAO) near2 (FUJIKI)).INV.	US-PGPUB; USPAT	OR	ON	2007/10/12 13:46
S38	18	((ATSUSHI) near2 (TANIGUCHI)).INV.	US-PGPUB; USPAT	OR	ON	2007/10/12 13:46
S39	8	((TAKASHI) near2 (GONDA)).INV.	US-PGPUB; USPAT	OR	ON	2007/10/12 13:46
S40	12	((KAZUTOKI) near2 (TAHARA)).INV.	US-PGPUB; USPAT	OR	ON	2007/10/12 13:47
S41	151	S36 or S37 or S38 or S39 or S40	US-PGPUB; USPAT	OR	ON	2007/10/12 13:48
S42	8	S41 and (electromagnetic or noise).clm.	US-PGPUB; USPAT	OR	ON	2007/10/12 13:49
S43	12	opposing near3 target near3 magnetron near3 sputtering	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/17 15:12
S44	106	opposing near3 target near3 sputtering	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/17 15:45

S45	18	opposing near3 target near3 magnetron	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/17 15:45
S46	6	S45 not S43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/17 15:45
S47	77812	deposition and (thickness same nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/18 12:10
S48	30281	deposition same (thickness same nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/18 12:11
S49	25169	sputtering same (thickness same nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/18 12:11
S50	2520	(magnetron near3 sputtering) same (thickness same nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/18 12:21
S51	2	(opposing near3 magnetron near3 sputtering) same (thickness same nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/18 12:12
S52	2164	S50 and metal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/18 12:12
S53	1204	S52 and (electromagnetic or EMF or rf)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/18 12:14
S54	803	S53 not (recording near3 medium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/18 12:15
S55	4752	electromagnetic near3 (noise or wave) near3 (suppressor or absorb or absorber or suppress)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/18 12:21
S56	16	(magnetron near3 sputtering) and S55	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/10/18 12:21
S57	8	("4784739" "5864088" "5990417" "6104530").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/15 14:21

S58	2	"20040219328"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/15 14:22
S59	27	((TOSHIYUKI) near2 (KAWAGUCHI)).INV.	US-PGPUB; USPAT	OR	ON	2008/05/15 14:52
S60	94	((HIRONAO) near2 (FUJIKI)).INV.	US-PGPUB; USPAT	OR	ON	2008/05/15 14:53
S61	20	((ATSUSHI) near2 (TANIGUCHI)).INV.	US-PGPUB; USPAT	OR	ON	2008/05/15 14:53
S62	8	((TAKASHI) near2 (GONDA)).INV.	US-PGPUB; USPAT	OR	ON	2008/05/15 14:54
S63	13	((KAZUTOKI) near2 (TAHARA)).INV.	US-PGPUB; USPAT	OR	ON	2008/05/15 14:54
S64	2301	(halogen near3 free) same (flame near3 retardant)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 10:09
S65	19	S64 same benefit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 10:09
S66	3	S65 and (nm or nanometer or (fine near3 particle))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 10:09
S67	45	electromagnetic near3 noise near3 suppressor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 10:10
S68	9	S67 and (nm or nanometer or (fine near3 particle))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 10:10
S69	3215	electromagnetic near3 radiation near3 (shield or shielding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 10:14
S70	498	S69 and (nm or nanometer or (fine near3 particle))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 10:14
S71	352017	(vapor near3 deposition) or vapor-deposition or cvd or pvd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 10:21
S72	134	S70 and S71	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 10:21

S73	2	"6869683"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 10:55
S74	2	"20030044623"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 10:56
S75	11541	204/192.1-192.38.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 13:21
S76	3812	S71 and S75	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 13:22
S77	2	S70 and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 13:22
S78	1281	S76 and (nm or nanometer or (fine near3 particle))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 13:24
S80	188157	(embed or embedding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 13:29
S81	8634	S71 and S80	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 13:29
S82	1492	S71 same S80	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 13:30
S83	500	S82 not (semiconductor near3 device)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/19 14:07
S84	10519	lattice and magnetic and (binder or polymer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/20 14:10
S85	2174	S84 and ((vapor near3 deposition) or pvd)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/20 14:10
S86	3335	lattice same ((vapor near3 deposition) or pvd)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/20 14:11

S87	167	S84 and S86	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/20 14:11
S88	3048	((physical near3 vapor near3 deposition) or pvd) and ((electron near3 volt) or ev)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/20 15:27
S89	832	S88 and magnetic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/20 15:27
S90	267	S89 and lattice	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/05/20 15:28
S91	2	"6869683"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/11/04 16:37
S92	27	((TOSHIYUKI) near2 (KAWAGUCHI)).INV.	US-PGPUB; USPAT	OR	ON	2008/11/04 17:00
S93	96	((HIRONAO) near2 (FUJIKI)).INV.	US-PGPUB; USPAT	OR	ON	2008/11/04 17:00
S94	20	((ATSUSHI) near2 (TANIGUCHI)).INV.	US-PGPUB; USPAT	OR	ON	2008/11/04 17:01
S95	8	((TAKASHI) near2 (GONDA)).INV.	US-PGPUB; USPAT	OR	ON	2008/11/04 17:02
S96	13	((KAZUTOKI) near2 (TAHARA)).INV.	US-PGPUB; USPAT	OR	ON	2008/11/04 17:02
S97	9	"5990417"	US-PGPUB; USPAT	OR	ON	2008/11/04 17:03
S98	1211	electromagnetic near3 noise near3 (shield or shielding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/11/04 17:10
S99	281865	(vapor near3 deposition) or vapor-deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/11/04 17:10
S100	60	S98 and S99	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/11/04 17:10
S101	42	S100 and (polymer or resin or rubber)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/11/04 17:10
S102	5445	electromagnetic near3 (noise or wave) near3 (suppressor or absorb or absorber or suppress)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/11 15:27

S103	21	(magnetron near3 sputtering) and S102	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/11 15:27
S104	61637	(noise or wave) near3 (suppressor or absorb or absorber or suppress)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/11 15:32
S105	342608	pvd or (vapor near3 deposit\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/11 15:32
S106	58	S104 same S105	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/11 15:32
S107	16	S106 and particle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/11 15:37
S108	22	("20040108486" "20040157085" "20040219328" "20060038630" "20060083948" "20070077369" "4784739" "5864088" "5990417" "6104530" "6869683" "7160636"). PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/11 16:04
S109	1352	S104 and S105	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/11 16:33
S110	112045	S109 and gigahertz or ghz	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/11 16:33
S111	269	S109 and (gigahertz or ghz)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/11 16:33
S112	69	S111 and resistivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/11 16:45
S113	61657	(noise or wave) near3 (suppressor or absorb or absorber or suppress)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/12 14:25
S114	342791	pvd or (vapor near3 deposit\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/12 14:25

S115	1353	S113 and S114	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/12 14:25
S116	99	S115 and eV	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/12 14:25
S117	8297	204/192.1-192.2.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/13 08:59
S118	623	S117 and (ev or (electron near3 volt))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/13 09:00
S119	339	S118 and (resistance or resistivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/13 09:00
S120	147	S118 and resistivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/13 09:02
S121	142895	anisotropic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/13 11:06
S122	15366	S121 and resistivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/13 11:07
S123	9206	S122 and crystal\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/13 11:07
S124	831	S123 and (ev or (electron near3 volt))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/13 11:08
S125	681	S124 and (nm or nanometer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/13 11:09
S126	189	S125 and (electromagnetic or emf or emi or rfi)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/13 11:13
S127	20	opposing near3 target near3 magnetron	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/14 11:26

S129	3937	428/411.1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/14 13:19
S130	381	S129 and (electromagnetic or emf or emi or rfi)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/14 13:20
S131	59	S130 and resistivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/05/14 14:10

5/ 21/ 2009 2:22:11 PM**C:\ Documents and Settings\erobinson\ My Documents\ EAST\ Workspaces\ 10540825.wsp**